

11/18/2005 10/708936 Doty

File 348:EUROPEAN PATENTS 1978-2005/Nov W01

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File 349:PCT FULLTEXT 1979-2005/UB=20051110,UT=20051103

(c) 2005 WIPO/Univentio

Set	Items	Description
S1	48878	TRISILICON TETRANITRIDE OR SILICON NITRIDE OR SIN OR SILICONITRIDE OR SI()NITRIDE OR SI3N4
S2	69636	TRISILICON()TETRANITRIDE OR SILICON()NITRIDE OR SIN OR SILICONITRIDE OR SI()NITRIDE OR SI3N4
S3	240133	SILICONDIOXIDE OR SILICON()DIOXIDE OR SILICON()OXIDE OR SILICA OR SIO OR SIO2
S4	1170986	VIA? ? OR STUD? ? OR PLUG? ? OR HOLE? ? OR APERTURE? ? OR - RIE OR REACTIVE()ION()ETCH??????? OR THROUGH()HOLE? ? OR SPUT- TER???? OR RECESS????
S5	197564	PHOTO(A) (RESIST??????? OR MASK??????? OR LITHOG??????? OR EN- GRAV??????? OR PHOTORESIST????? OR PHOTOMASK??????????? OR PHOT- OLITHO??????? OR PHOTOENGRAV????? OR MASK????? OR LITHOG??????? OR ENGRAV??????? OR ETCH? OR BOE
S6	237155	OXIDAT??????? OR LOCOS OR OXIDI????? OR OXIDIZ?????
S7	567220	(BOTH OR MULTIPLE? ? OR BACK OR UNDER OR DOUBLE??? OR TWO - OR 2 OR DUPLICAT???? OR FIRST OR SECOND) (2W) (SIDE??? OR SURFA- CE??? OR SUBSTRATE? ? OR LAYER? ?) OR UNDERSIDE??? OR UNDERET- CH??? OR BACKSIDE OR BOTTOM()UP
S8	40709	S4 (5N) S7
S9	969	S1 (5N) S5
S10	5023	S2 (5N) (S5 OR S6)
S11	231	S8 AND S9 AND S10
S12	209	S11 AND S3
S13	35	S12/TI,AB,CL
S14	109	S12/TI,AB,CM
S15	1247	IC=(B81B-007/00 OR B81C-001/00 OR H01L-021/78)
S16	1	S14 AND S15
S17	2	S15 AND S12
S18	1	S17 NOT S16
S19	23	S1 AND S2 AND S3 AND S4 AND S5 AND S6 AND S7 AND S15
S20	22	S19 NOT S17
S21	108	S14 NOT S19
S22	1806	(CAP???? OR GLASS??) () (DIE? ? OR WAFER? ?)
S23	4	S21 AND S22
S24	16857	PACKAG??????? (5N) (CHIP? ? OR MICROCHIP? ? OR WAFER? ? OR IC OR INTEGRAT????()CIRCUIT? ? OR TRANSISTOR? ? OR SEMICONDUCT??- ???)
S25	12	S21 AND S24
S26	12	S25 NOT S23
S27	222231	(MATING OR MATE OR MALE(N) FEMALE OR STACK?????)
S28	38	S21 AND S27
S29	32	S28 NOT (S26 OR S19)

EIC 2800 MARY S. MIMS 272-5928

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20/5/5 (Item 5 from file: 348)  
DIALOG(R) File 348:EUROPEAN PATENTS  
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01656665

Method of fabrication of a microfluidic device  
Verfahren zur Herstellung eines mikrofluidischen Bauteiles  
Methode de fabrication d'un dispositif microfluidique

PATENT ASSIGNEE:

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Enschede, (NL), (Applicant designated States: all)

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PATENT (CC, No, Kind, Date): EP 1362827 A1 031119 (Basic)

APPLICATION (CC, No, Date): EP 2002076937 020516;

DESIGNATED STATES: AT; BE; CH; CY; DE; DK; ES; FI; FR; GB; GR; IE; IT; LI;  
LU; MC; NL; PT; SE; TR

EXTENDED DESIGNATED STATES: AL; LT; LV; MK; RO; SI

INTERNATIONAL PATENT CLASS: B81B-001/00; B81C-001/00

ABSTRACT EP 1362827 A1

The present invention relates to a method of fabricating a microfluidic device including at least two substrates provided with a fluid channel, comprising the steps of:

a) etching at least a channel and one or more fluid ports in a first and/or a second substrate;

b) depositing a first layer on a surface of the second substrate;

c) partially removing the first layer in accordance with a predefined geometry;

d) depositing a second layer on top of the first layer and the substrate surface;

e) planarizing the second layer so as to smooth the upper surface thereof;

f) aligning the first and second substrate;

g) bonding the first substrate on the planarized second layer of the second substrate.

ABSTRACT WORD COUNT: 126

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20/5/6 (Item 6 from file: 348)  
DIALOG(R) File 348:EUROPEAN PATENTS  
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01640442

Semiconductor device comprising a flexible region and method for manufacturing the same

Halbleitervorrichtung mit flexiblem Bereich und Herstellungsverfahren

Dispositif semi-conducteur comprenant une region flexible, et procede de fabrication associe

PATENT ASSIGNEE:

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INVENTOR:

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LEGAL REPRESENTATIVE:

Muller - Hoffmann & Partner (101521), Patentanwalte, Innere Wiener  
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PATENT (CC, No, Kind, Date): EP 1351292 A2 031008 (Basic)  
EP 1351292 A3 040421

APPLICATION (CC, No, Date): EP 2003007696 030403;

PRIORITY (CC, No, Date): JP 2002104374 020405

DESIGNATED STATES: DE; FR

EXTENDED DESIGNATED STATES: AL; LT; LV; MK

INTERNATIONAL PATENT CLASS: H01L-021/78; H01L-021/762; H01L-029/786;  
H01L-051/20; G02F-001/1333

ABSTRACT EP 1351292 A2

A semiconductor device comprising a semiconductor layer and one, or a plurality of, semiconductor elements formed on a surface of the semiconductor layer, characterized in that said semiconductor layer is divided into a plurality of pieces in a region wherein said semiconductor layer does not have a semiconductor element and in that the respective pieces of the divided semiconductor layer have a flexible region made of an insulating layer adhered to the sides of the respective pieces so that the pieces are integrated.

ABSTRACT WORD COUNT: 84

11/18/2005 10/708936 Doty

20/5/16 (Item 3 from file: 349)  
DIALOG(R) File 349:PCT FULLTEXT  
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01036762 \*\*Image available\*\*

MICROENGINEERED ELECTRICAL CONNECTORS  
CONNECTEURS ELECTRIQUES FABRIQUES PAR LA TECHNOLOGIE MEMS  
Patent Applicant/Assignee:

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Patent Applicant/Inventor:

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Legal Representative:

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Patent and Priority Information (Country, Number, Date):

Patent: WO 200366515 A2-A3 20030814 (WO 0366515)  
Application: WO 2003GB314 20030127 (PCT/WO GB0300314)  
Priority Application: GB 20023047 20020208

Main International Patent Class: B81C-001/00

International Patent Class: B81C-003/00; B81B-007/00; H01R-043/00

Publication Language: English

Filing Language: English

Fulltext Availability:

Detailed Description  
Claims

Fulltext Word Count: 7339

English Abstract

A miniature, multi-element electrical connector fabricated using micro-electro-mechanical systems technology is described. Shaped elastic cantilever elements (12) are formed on the female part (11) by deposition of conducting material on a surface that has been previously shaped to define a localised contact area and a sloped entrance face. The cantilevers (12) are then undercut. A similar process is used to construct a sloping face on the male part (10) for easy insertion. An etching process is used to fabricate an interlocking alignment system (20, 21, 22) on the two parts. Erosion of a convex corner is used to form a tapered entrance (22) to this alignment system.

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20/5/20 (Item 7 from file: 349)  
DIALOG(R)File 349:PCT FULLTEXT  
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00988093 \*\*Image available\*\*

MEMS AND METHOD OF MANUFACTURING MEMS

MEMS ET PROCEDE DE PRODUCTION DE MEMS

Patent Applicant/Assignee:

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Patent Applicant/Inventor:

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Legal Representative:

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Patent and Priority Information (Country, Number, Date):

Patent: WO 200316205 A2-A3 20030227 (WO 0316205)

Application: WO 2002US26090 20020815 (PCT/WO US02026090)

Priority Application: US 2001312659 20010815

Main International Patent Class: B81C-001/00

International Patent Class: B81C-005/00; H01L-021/78

Publication Language: English

Filing Language: English

Fulltext Availability:

Detailed Description

Claims

Fulltext Word Count: 12340

English Abstract

The present invention relates to micro electro-mechanical systems (MEMS) and production methods thereof, and more particularly to vertically integrated MEMS systems. Manufacturing of MEMS and vertically integrated MEMS is facilitated by forming, preferably on a wafer level, plural MEMS on a MEMS layer selectively bonded to a substrate, and removing the MEMS layer intact.

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26/5/12 (Item 5 from file: 349)  
DIALOG(R) File 349:PCT FULLTEXT  
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00183345

FABRICATING ELECTRONIC CIRCUITRY UNIT CONTAINING STACKED IC LAYERS HAVING  
LEAD REROUTING :  
PRODUCTION D'UNITES DE CIRCUITS ELECTRONIQUES CONTENANT DES COUCHES  
EMPILEES DE CIRCUITS INTEGRES A REACHEMINEMENT DES CONDUCTEURS

Patent Applicant/Assignee:

IRVINE SENSORS CORPORATION,

Inventor(s):

GO Tiang C +di,  
MINIHAN Joseph A,  
SHANKEN Stuart N,

Patent and Priority Information (Country, Number, Date):

Patent: WO 9100683 A2 19910124

Application: WO 90US3705 19900628 (PCT/WO US9003705)

Priority Application: US 89241 19890707

Designated States:

(Protection type is "patent" unless otherwise stated - for applications  
prior to 2004)

AT BE CH DE DK ES FR GB IT JP LU NL SE

Publication Language: English

Fulltext Availability:

Detailed Description

Claims

Fulltext Word Count: 8173

English Abstract

A process and product are disclosed which apply advanced concepts of Z-technology to the field of dense electronic packages. Starting with standard chip-containing silicon wafers (fig. 1, 20), modification procedures are followed which create IC chips (fig. 4, 38) having rerouted gold leads (fig. 4, 30) on top of passivation (fig. 6, 52) (which covers the original silicon (fig. 6, 48) and its aluminum or other metallization (fig. 6, 44)). The modified chips (fig. 4, 38) are cut from the wafers (fig. 1, 20), and then stacked to form multi-layer IC devices (fig. 10b, 60). A stack has one or more access planes (fig. 10c, 64). After stacking, and before applying gold metallization on the access plane, a selective etching step removes any aluminum (or other material) which might interfere with the gold metallization formed on the access planes (figs. 11 and 12). Gold terminal pads (fig. 15, 92) are formed in contact with the terminals of the gold rerouting leads (fig. 15, 66) on the stacked chips, thereby forming gold-to-gold T-connections (fig. 14) for maximum conducting efficiency.

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23/5/4 (Item 4 from file: 349)  
DIALOG(R) File 349:PCT FULLTEXT  
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00519553 \*\*Image available\*\*

WAFER-PAIR HAVING DEPOSITED LAYER SEALED CHAMBERS  
PAIRE DE TRANCHES FORMANT DES CAVITES HERMETIQUES COMBLEES PAR DEPOT D'UNE  
COUCHE

Patent Applicant/Assignee:

HONEYWELL INC,

Inventor(s):

WOOD R Andrew,

RIDLEY Jeffrey A,

HIGASHI Robert E,

Patent and Priority Information (Country, Number, Date):

Patent: WO 9950905 A1 19991007

Application: WO 99US6790 19990329 (PCT/WO US9906790)

Priority Application: US 9852630 19980331

Designated States:

(Protection type is "patent" unless otherwise stated - for applications  
prior to 2004)

CA JP AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Main International Patent Class: H01L-023/10

Publication Language: English

Fulltext Availability:

Detailed Description

Claims

Fulltext Word Count: 3496

English Abstract

A wafer-pair having at least one recess in one wafer forms at least one chamber with the attaching of the other wafer which has at least one port which is plugged with a deposited layer on its external surface. The deposition of the layer may be performed in a very low pressure environment, thus assuring the same kind of environment in the sealed chamber. The chamber may enclose at least one device such as a thermoelectric sensor, bolometer, emitter or other kind of device. The wafer-pair typically will have numerous chambers, and may be divided into chips.

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23/5/3 (Item 3 from file: 349)  
DIALOG(R)File 349:PCT FULLTEXT  
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00519561 \*\*Image available\*\*  
A METHOD OF MAKING A WAFER-PAIR HAVING SEALED CHAMBERS  
PROCEDE DE PRODUCTION D'UNE PAIRE DE TRANCHES POSSEDANT DES ENCEINTES  
CLOSES

Patent Applicant/Assignee:

HONEYWELL INC,

Inventor(s):

WOOD R Andrew,

RIDLEY Jeffrey A,

HIGASHI Robert E,

Patent and Priority Information (Country, Number, Date):

Patent: WO 9950913 A1 19991007

Application: WO 99US6890 19990330 (PCT/WO US9906890)

Priority Application: US 9852645 19980331

Designated States:

(Protection type is "patent" unless otherwise stated - for applications  
prior to 2004)

CA JP AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Main International Patent Class: H01L-027/16

International Patent Class: G01J-005/20

Publication Language: English

Fulltext Availability:

Detailed Description

Claims

Fulltext Word Count: 4243

English Abstract

A method for fabricating a wafer-pair having at least one recess in one wafer and the recess formed into a chamber with the attaching of the other wafer which has a port plugged with a deposited layer on its external surface. The deposition of the layer may be performed in a very low pressure environment, thus assuring the same kind of environment in the sealed chamber. The chamber may enclose at least one device such as a thermoelectric sensor, bolometer, emitter or other kind of device. The wafer-pair typically will have numerous chambers, with devices, respectively, and may be divided into a multiplicity of chips.